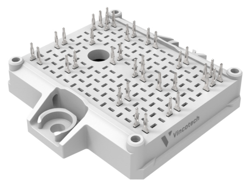
10-EY122PA005ME-LU39F08T
datasheet

***flow*Dual E2 SiC** **1200 V / 5 mΩ**

Features

- C3M™ SiC MOSFET technology
- Standard industrial housing
- Low inductive design
- Optimized Rth(j-s) with Phase Change Material
- Built-in NTC

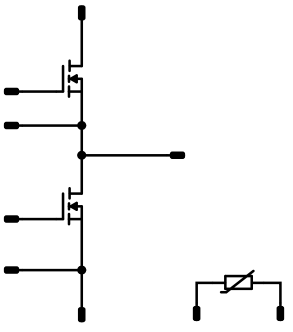
flow E2 12 mm housing



Target applications

- Charging Stations
- Energy Storage Systems
- Power Supply
- Solar Inverters
- Welding & Cutting

Schematic



Types

- 10-EY122PA005ME-LU39F08T

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Half-Bridge Switch - Lo side					
Drain-source voltage	V_{DSS}			1200	V
Drain current (DC current)	I_D	$T_j = T_{jmax}$	T_s = 80 °C	182	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}		720	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	303	W
Gate-source voltage	V_{GSS}			-4 / 15	V
		dynamic		-8 / 19	
Maximum Junction Temperature	T_{jmax}			175	°C
Half-Bridge Switch - Hi side					
Drain-source voltage	V_{DSS}			1200	V
Drain current (DC current)	I_D	$T_j = T_{jmax}$	T_s = 80 °C	182	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}		720	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	303	W
Gate-source voltage	V_{GSS}			-4 / 15	V
		dynamic		-8 / 19	
Maximum Junction Temperature	T_{jmax}			175	°C
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				min. 12,7	mm
Clearance				9,34	mm
Comparative Tracking Index	CTI			≥ 600	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Half-Bridge Switch - Lo side										
Static										
Drain-source on-state resistance	$r_{DS(on)}$		15		240	25 125 150	3,73	7 8 9	6,93(1)	mΩ
Gate-source threshold voltage	$V_{GS(th)}$		0		0,069	25	1,8	2,5	3,6	V
Gate to Source Leakage Current	I_{GSS}		15	0		25		60	1500	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25		6	114	µA
Internal gate resistance	r_g							0,283		Ω
Gate charge	Q_g		-4/15	800	240	25		708		nC
Short-circuit input capacitance	C_{iss}	f = 100 kHz	0	1000	0	25		20142		pF
Short-circuit output capacitance	C_{oss}							774		
Reverse transfer capacitance	C_{rss}							48		
Diode forward voltage	V_{SD}		0		120	25		4,6		V
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,31		K/W

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 5,8 Ω R_{goff} = 5,8 Ω	-4/15	600	240	25 125 150		81,92 72,96 71,36		ns
Rise time	t_r					25 125 150		44,16 38,08 37,44		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		176 192,64 196,8		ns
Fall time	t_f					25 125 150		19,13 19,67 20,12		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=1,18 µC Q_{rFWD}=3 µC Q_{rFWD}=3,46 µC				25 125 150		7,14 6,92 7,06		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		4,96 4,89 4,95		mWs
Peak recovery current	I_{RRM}	di/dt=6563 A/µs di/dt=7498 A/µs di/dt=7673 A/µs				25 125 150		70,69 121,3 135,34		A
Reverse recovery time	t_{rr}					25 125 150		24,01 41,34 43,89		ns
Recovered charge	Q_r					25 125 150		1,18 3 3,46		µC
Reverse recovered energy	E_{rec}					25 125 150		0,315 0,821 0,972		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		8511 7629 7909		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Half-Bridge Switch - Hi side										
Static										
Drain-source on-state resistance	$r_{DS(on)}$		15		240	25 125 150	3,73	7 8 9	6,93 (1)	mΩ
Gate-source threshold voltage	$V_{GS(th)}$		0		0,069	25	1,8	2,5	3,6	V
Gate to Source Leakage Current	I_{GSS}		15	0		25		60	1500	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25		6	114	µA
Internal gate resistance	r_g							0,283		Ω
Gate charge	Q_g		-4/15	800	240	25		708		nC
Short-circuit input capacitance	C_{iss}	f = 100 kHz	0	1000	0	25		20142		pF
Short-circuit output capacitance	C_{oss}							774		
Reverse transfer capacitance	C_{rss}							48		
Diode forward voltage	V_{SD}		0		120	25		4,6		V
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,31		K/W

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Dynamic										
Turn-on delay time	$t_{d(on)}$					25 125 150		81,92 72,96 71,36		ns
Rise time	t_r	R_{gon} = 5,8 Ω R_{goff} = 5,8 Ω				25 125 150		44,16 38,08 37,44		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		176 192,64 196,8		ns
Fall time	t_f					25 125 150		19,13 19,67 20,12		ns
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Reverse recovered energy	E_{rec}					25 125 150		0,315 0,821 0,972		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		8511 7629 7909		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 493 Ω				100	-5		5	%
Power dissipation	P							245		mW
Power dissipation constant	d					25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. ±2 %						3375		K
B-value	$B_{(25/100)}$	Tol. ±2 %						3437		K
Vincotech Thermistor Reference									K	

(1) Value at chip level

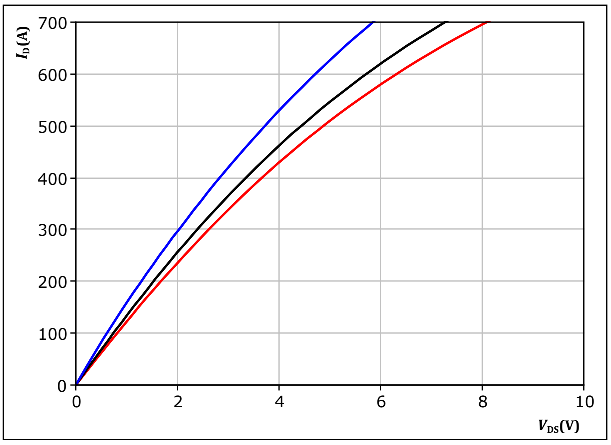
(2) Only valid with pre-applied Vincotech thermal interface material.

Half-Bridge Switch - Lo side Characteristics

figure 1. MOSFET

Typical output characteristics

$I_D = f(V_{DS})$

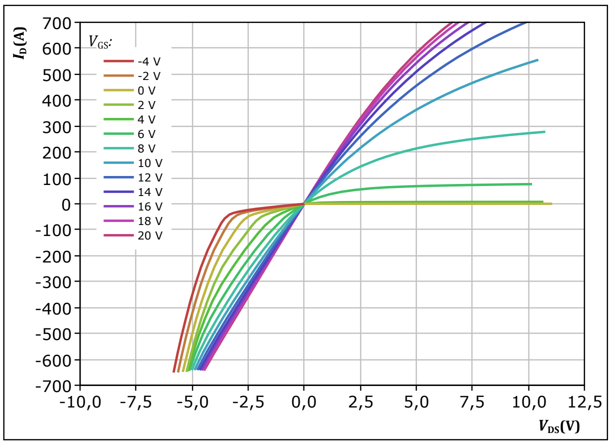


t_p = 250 µs
V_{GS} = 14 V
T_j: 25 °C, 125 °C, 150 °C

figure 2. MOSFET

Typical output characteristics

$I_D = f(V_{DS})$

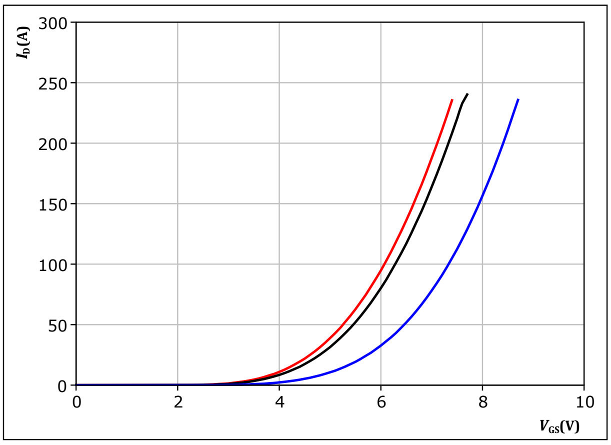


t_p = 250 µs
T_j = 150 °C
V_{GS} from -4 V to 20 V in steps of 2 V

figure 3. MOSFET

Typical transfer characteristics

$I_D = f(V_{GS})$

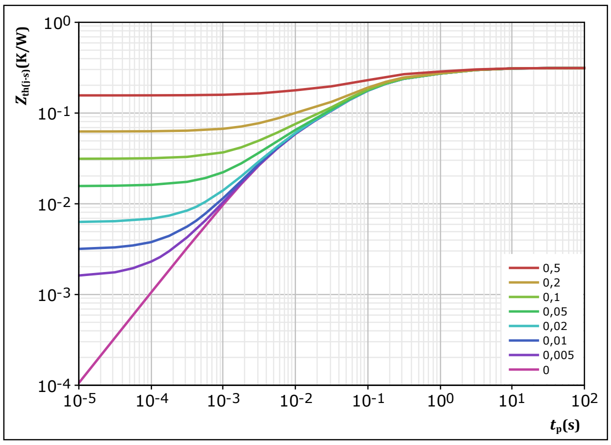


t_p = 250 µs
V_{DS} = 10 V
T_j: 25 °C, 125 °C, 150 °C

figure 4. MOSFET

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T
$R_{th(j-s)}$ = 0,313 K/W

MOSFET thermal model values

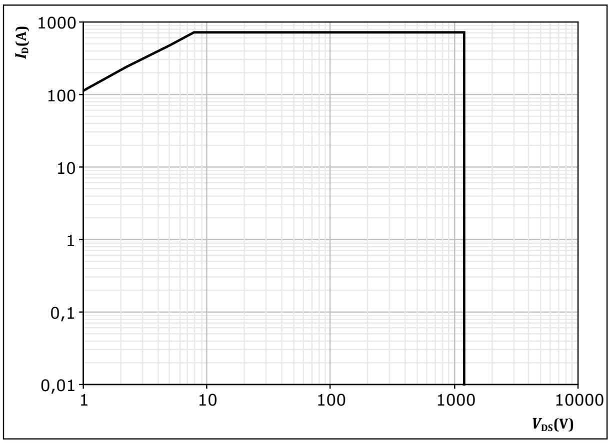
R (K/W)	τ (s)
2,18E-02	4,91E+00
5,79E-02	1,09E+00
1,25E-01	1,28E-01
7,04E-02	3,88E-02
3,80E-02	4,91E-03

Half-Bridge Switch - Lo side Characteristics

figure 5. **MOSFET**

Safe operating area

I_D = f(V_{DS})



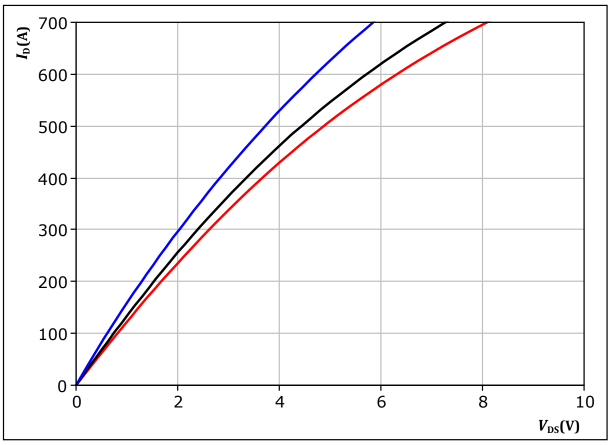
D =	single pulse	
T_s =	80	°C
V_{GS} =	14	V
T_j =	T_{jmax}	

Half-Bridge Switch - Hi side Characteristics

figure 6. **MOSFET**

Typical output characteristics

I_D = f(V_{DS})

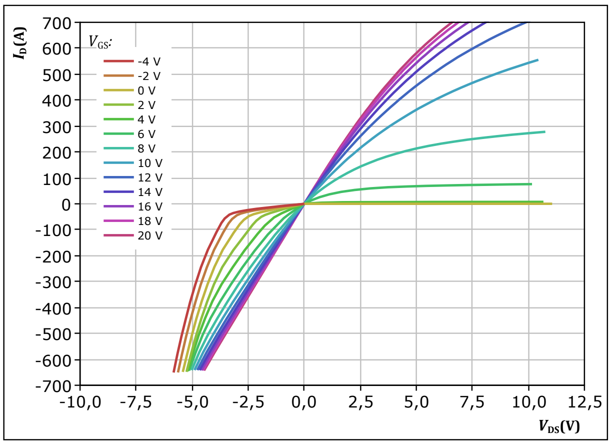


t_p = 250 µs
V_{GS} = 14 V
T_j: 25 °C, 125 °C, 150 °C

figure 7. **MOSFET**

Typical output characteristics

I_D = f(V_{DS})

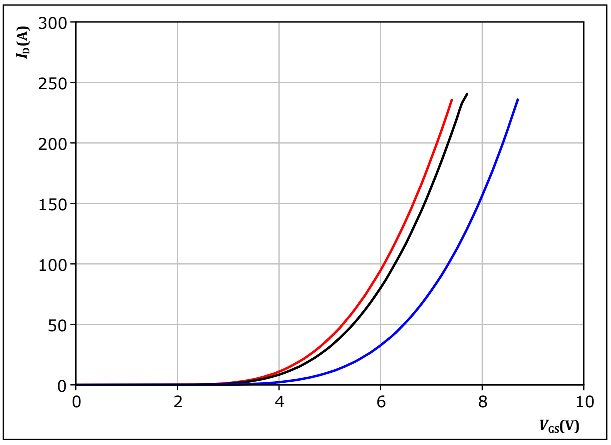


t_p = 250 µs
T_j = 150 °C
V_{GS} from -4 V to 20 V in steps of 2 V

figure 8. **MOSFET**

Typical transfer characteristics

I_D = f(V_{GS})

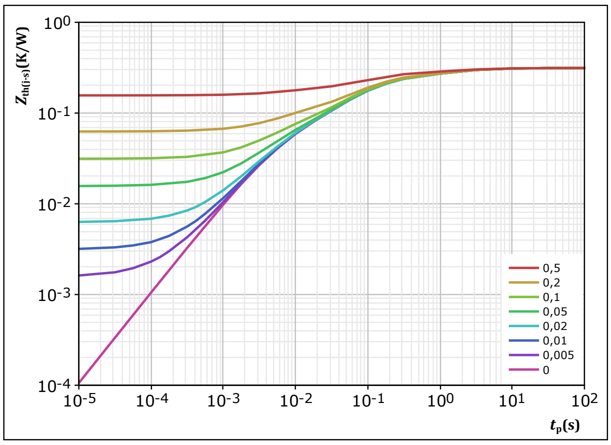


t_p = 250 µs
V_{DS} = 10 V
T_j: 25 °C, 125 °C, 150 °C

figure 9. **MOSFET**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T
$R_{th(j-s)}$ = 0,313 K/W

MOSFET thermal model values

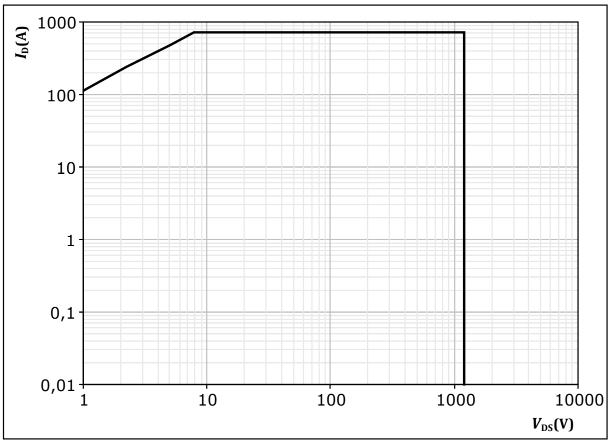
R (K/W)	τ (s)
2,18E-02	4,91E+00
5,79E-02	1,09E+00
1,25E-01	1,28E-01
7,04E-02	3,88E-02
3,80E-02	4,91E-03

Half-Bridge Switch - Hi side Characteristics

figure 10. **MOSFET**

Safe operating area

$I_D = f(V_{DS})$



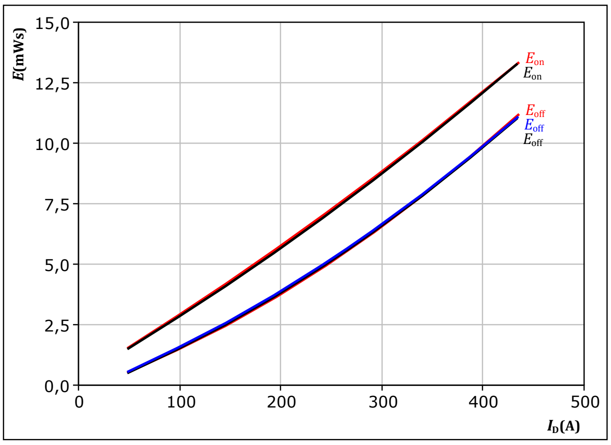
D =	single pulse	
T_s =	80	°C
V_{GS} =	14	V
T_j =	T_{jmax}	

Half-Bridge Switching Characteristics - Lo side

figure 11. MOSFET

Typical switching energy losses as a function of drain current

$E = f(I_D)$



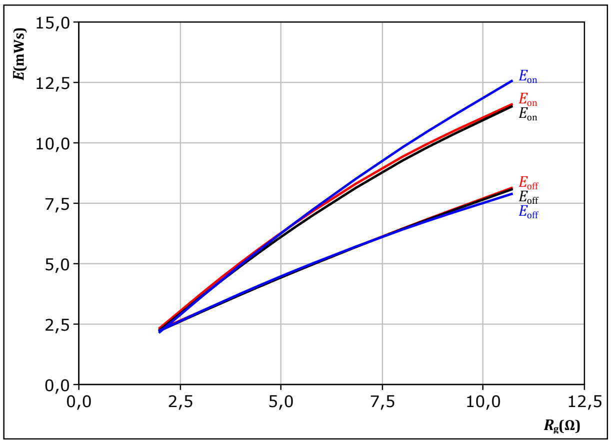
With an inductive load at

V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
R_{gon} =	5,8	Ω		150 °C
R_{goff} =	5,8	Ω		

figure 12. MOSFET

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



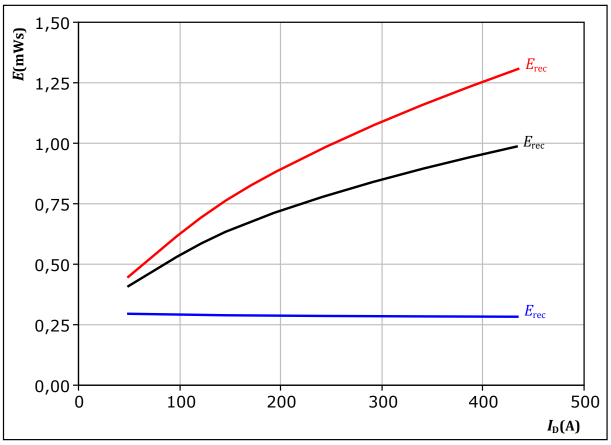
With an inductive load at

V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
I_D =	240	A		150 °C

figure 13. MOSFET

Typical reverse recovered energy loss as a function of drain current

$E_{rec} = f(I_D)$



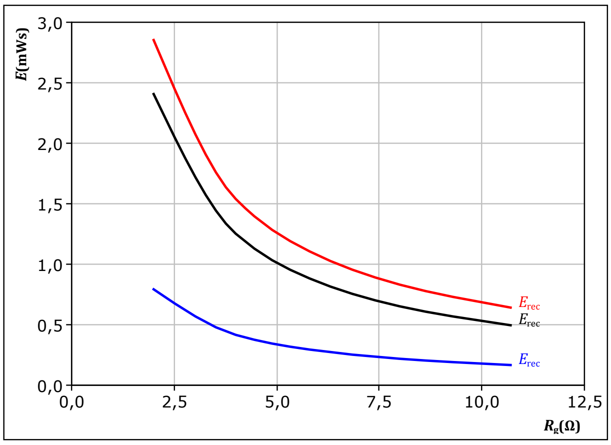
With an inductive load at

V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
R_{gon} =	5,8	Ω		150 °C

figure 14. MOSFET

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

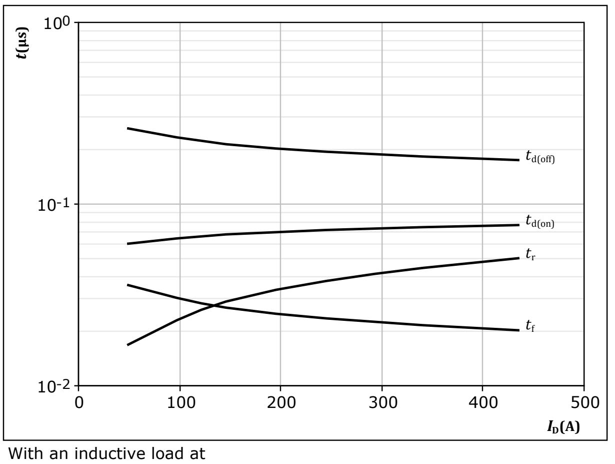
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
I_D =	240	A		150 °C

Half-Bridge Switching Characteristics - Lo side

figure 15. **MOSFET**

Typical switching times as a function of drain current

t = f(I_D)



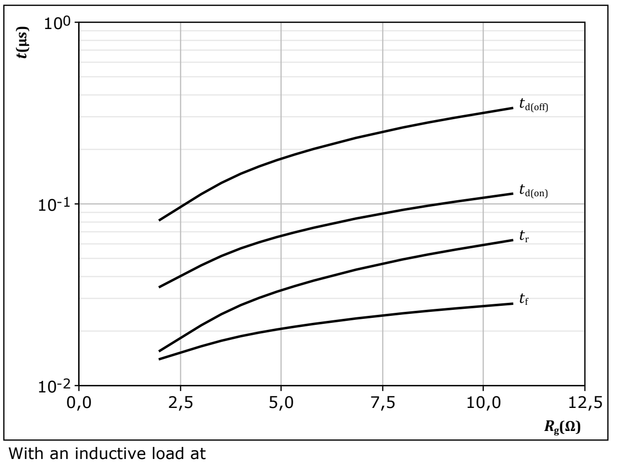
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-4/15	V
R_{gon} =	5,8	Ω
R_{goff} =	5,8	Ω

figure 16. **MOSFET**

Typical switching times as a function of gate resistor

t = f(R_g)



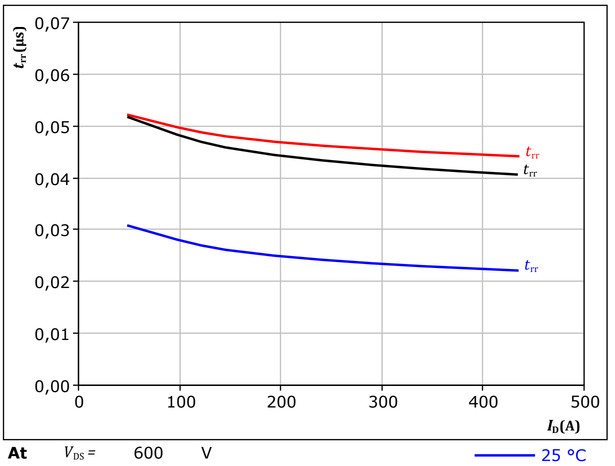
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-4/15	V
I_D =	240	A

figure 17. **MOSFET**

Typical reverse recovery time as a function of drain current

t_{rr} = f(I_D)



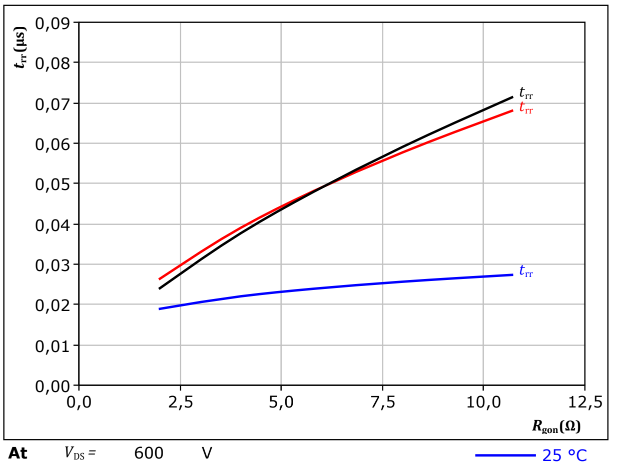
At	V_{DS} =	600	V	
	V_{GS} =	-4/15	V	
	R_{gon} =	5,8	Ω	

T_j: 25 °C / 125 °C / 150 °C

figure 18. **MOSFET**

Typical reverse recovery time as a function of turn on gate resistor

t_{rr} = f(R_{gon})



At	V_{DS} =	600	V
	V_{GS} =	-4/15	V
	I_D =	240	A

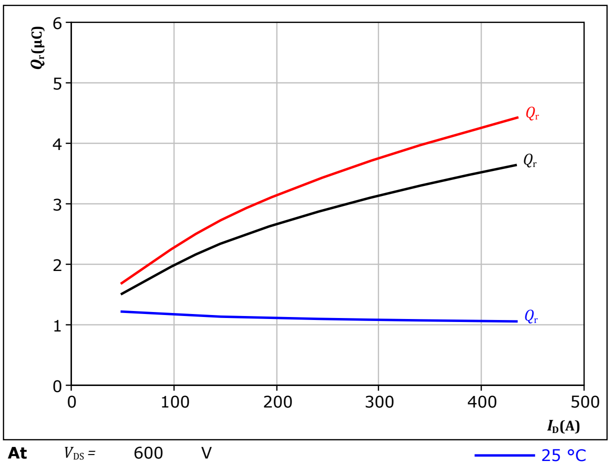
T_j: 25 °C / 125 °C / 150 °C

Half-Bridge Switching Characteristics - Lo side

figure 19. **MOSFET**

Typical recovered charge as a function of drain current

Q_r = f(I_D)

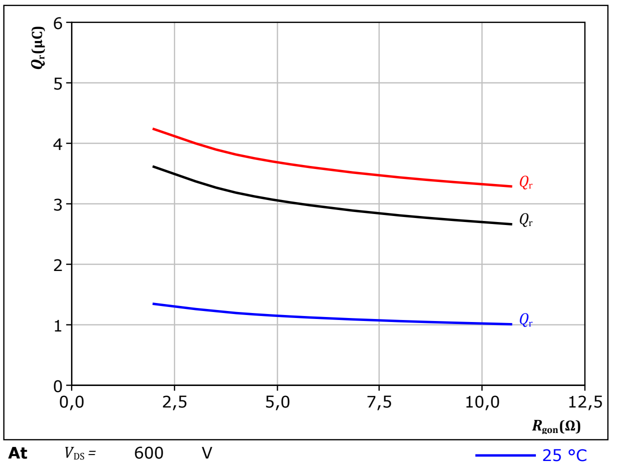


At	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/15	V	T_j:	125 °C
	R_{gon} =	5,8	Ω		150 °C

figure 20. **MOSFET**

Typical recovered charge as a function of turn on gate resistor

Q_r = f(R_{gon})

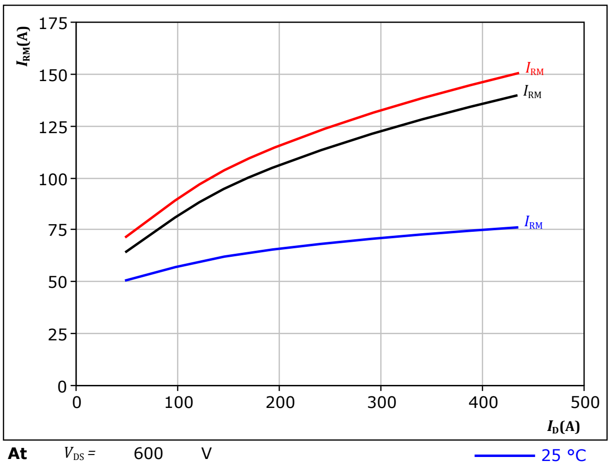


At	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/15	V	T_j:	125 °C
	I_D =	240	A		150 °C

figure 21. **MOSFET**

Typical peak reverse recovery current as a function of drain current

I_{RM} = f(I_D)

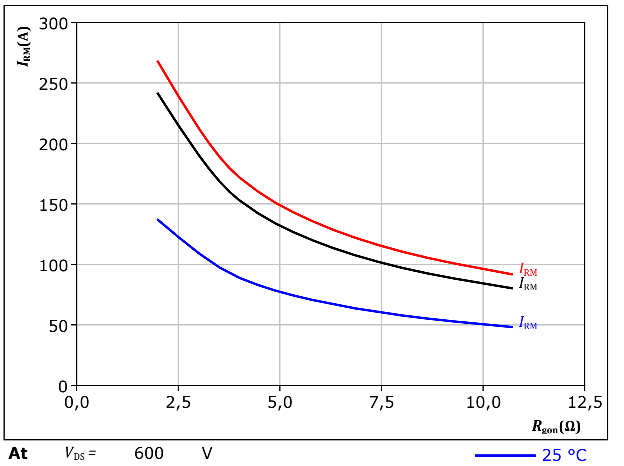


At	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/15	V	T_j:	125 °C
	R_{gon} =	5,8	Ω		150 °C

figure 22. **MOSFET**

Typical peak reverse recovery current as a function of turn on gate resistor

I_{RM} = f(R_{gon})



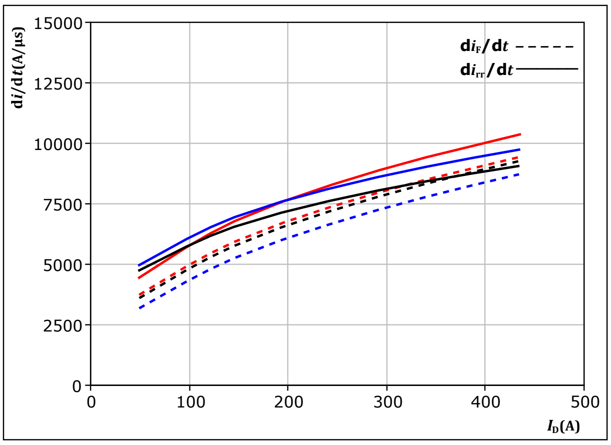
At	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/15	V	T_j:	125 °C
	I_D =	240	A		150 °C

Half-Bridge Switching Characteristics - Lo side

figure 23. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of drain current

di_F/dt, di_{rr}/dt = f(I_D)

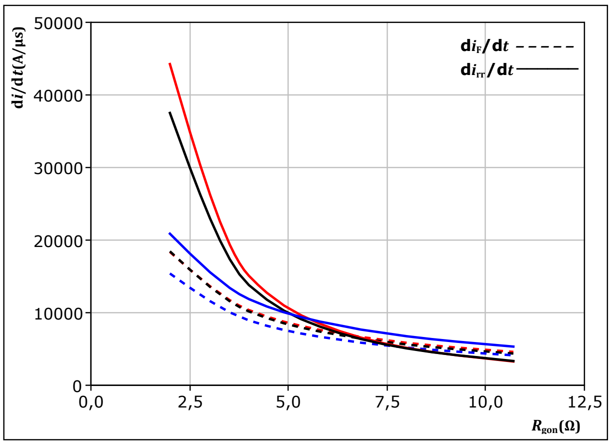


At					
	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/15	V	T_j:	125 °C
	R_{gon} =	5,8	Ω		150 °C

figure 24. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})

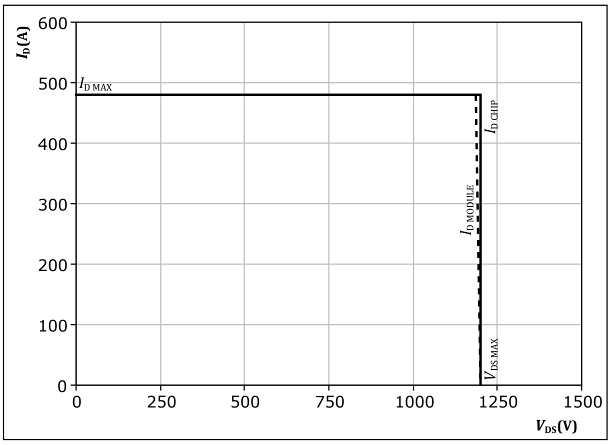


At					
	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/15	V	T_j:	125 °C
	I_D =	240	A		150 °C

figure 25. **MOSFET**

Reverse bias safe operating area

I_D = f(V_{DS})



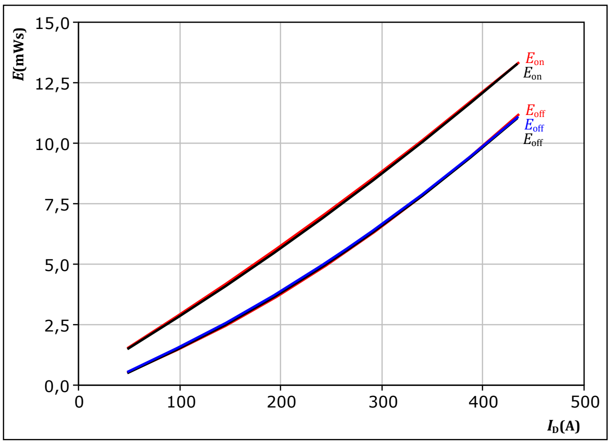
At			
	T_j =	150	°C
	R_{gon} =	5,8	Ω
	R_{goff} =	5,8	Ω

Half-Bridge Switching Characteristics - Hi side

figure 26. MOSFET

Typical switching energy losses as a function of drain current

$E = f(I_D)$



With an inductive load at

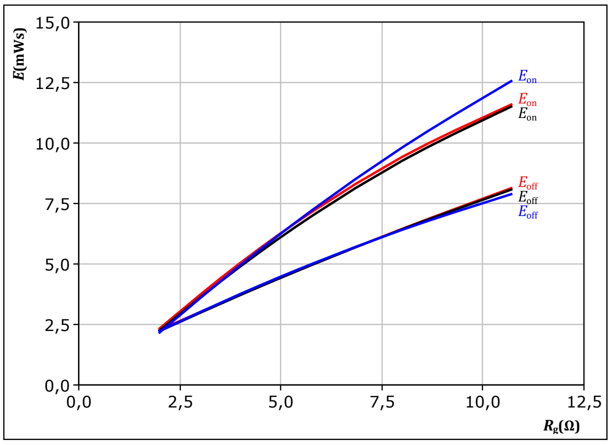
V_{DS} =	600	V	
V_{GS} =	-4/15	V	
R_{gon} =	5,8	Ω	
R_{goff} =	5,8	Ω	

T_j: 25 °C, 125 °C, 150 °C

figure 27. MOSFET

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



With an inductive load at

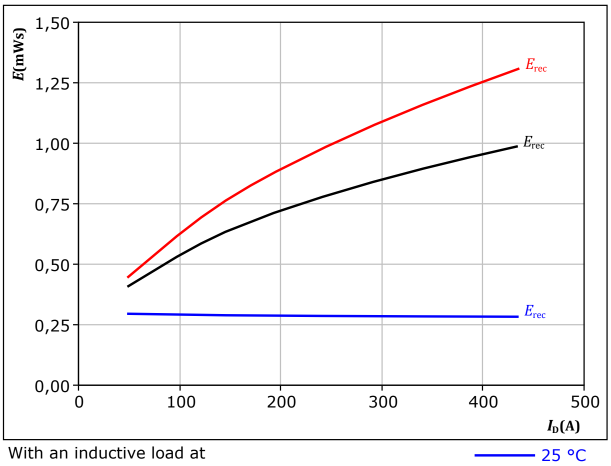
V_{DS} =	600	V
V_{GS} =	-4/15	V
I_D =	240	A

T_j: 25 °C, 125 °C, 150 °C

figure 28. MOSFET

Typical reverse recovered energy loss as a function of drain current

$E_{rec} = f(I_D)$



With an inductive load at

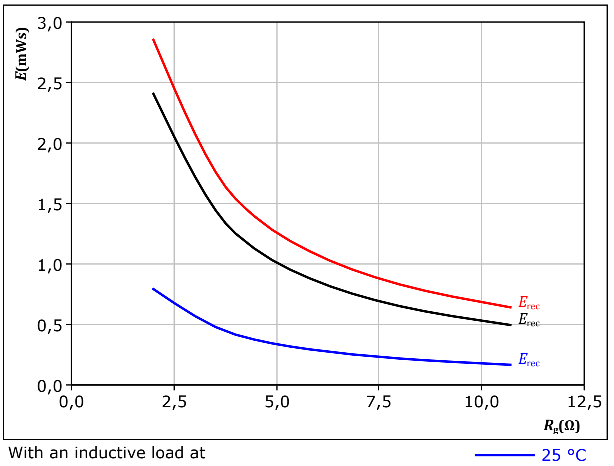
V_{DS} =	600	V
V_{GS} =	-4/15	V
R_{gon} =	5,8	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 29. MOSFET

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

V_{DS} =	600	V
V_{GS} =	-4/15	V
I_D =	240	A

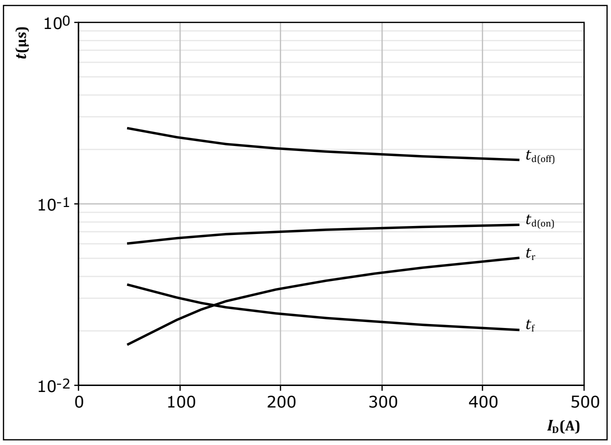
T_j: 25 °C, 125 °C, 150 °C

Half-Bridge Switching Characteristics - Hi side

figure 30. MOSFET

Typical switching times as a function of drain current

t = f(I_D)



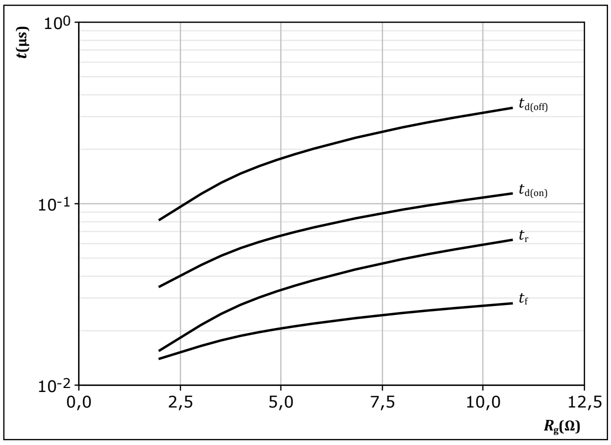
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-4/15	V
R_{gon} =	5,8	Ω
R_{goff} =	5,8	Ω

figure 31. MOSFET

Typical switching times as a function of gate resistor

t = f(R_g)



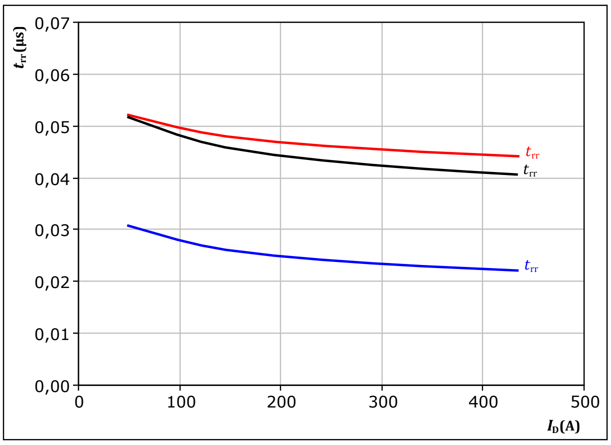
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-4/15	V
I_D =	240	A

figure 32. MOSFET

Typical reverse recovery time as a function of drain current

t_{rr} = f(I_D)



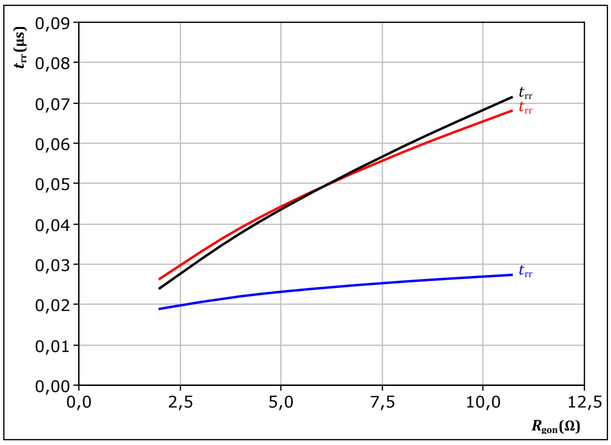
At			
	V_{DS} =	600	V
	V_{GS} =	-4/15	V
	R_{gon} =	5,8	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 33. MOSFET

Typical reverse recovery time as a function of turn on gate resistor

t_{rr} = f(R_{gon})



At			
	V_{DS} =	600	V
	V_{GS} =	-4/15	V
	I_D =	240	A

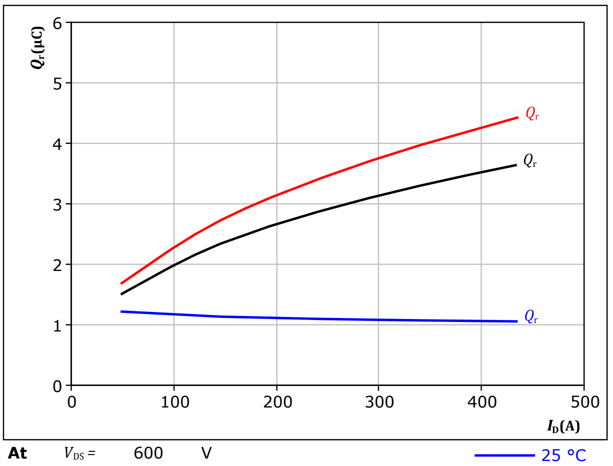
T_j: 25 °C, 125 °C, 150 °C

Half-Bridge Switching Characteristics - Hi side

figure 34. MOSFET

Typical recovered charge as a function of drain current

Q_r = f(I_D)

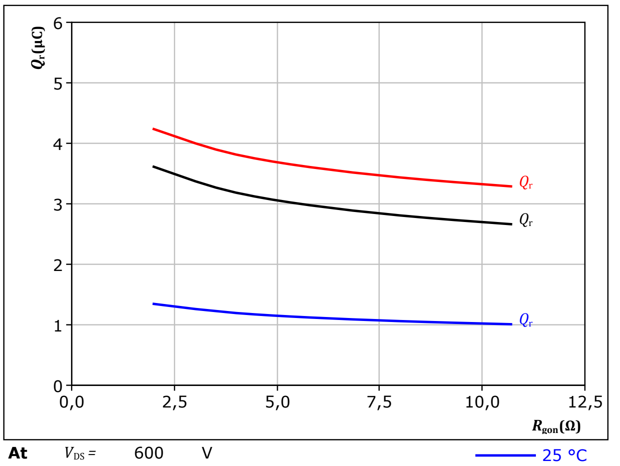


At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
R_{gon} =	5,8	Ω		150 °C

figure 35. MOSFET

Typical recovered charge as a function of turn on gate resistor

Q_r = f(R_{gon})

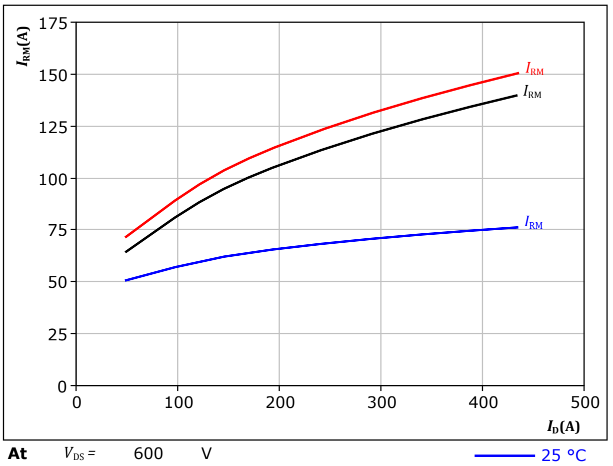


At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
I_D =	240	A		150 °C

figure 36. MOSFET

Typical peak reverse recovery current as a function of drain current

I_{RM} = f(I_D)

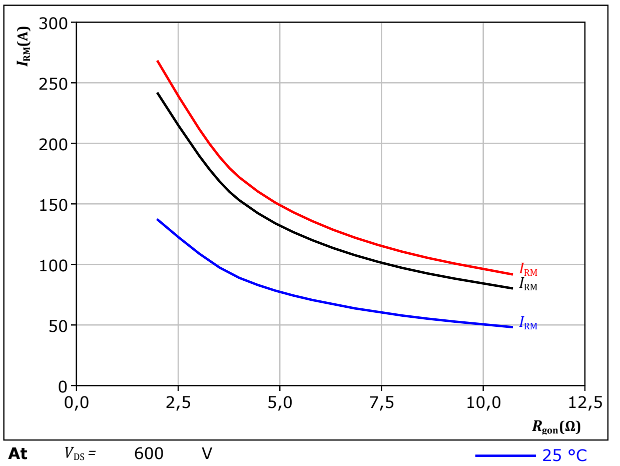


At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
R_{gon} =	5,8	Ω		150 °C

figure 37. MOSFET

Typical peak reverse recovery current as a function of turn on gate resistor

I_{RM} = f(R_{gon})



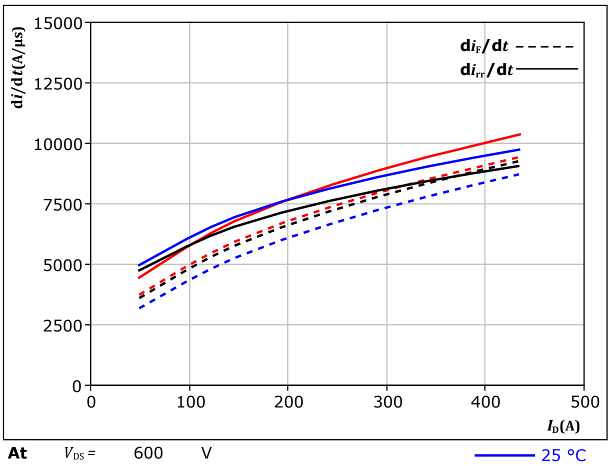
At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
I_D =	240	A		150 °C

Half-Bridge Switching Characteristics - Hi side

figure 38. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of drain current

di_F/dt, di_{rr}/dt = f(I_D)

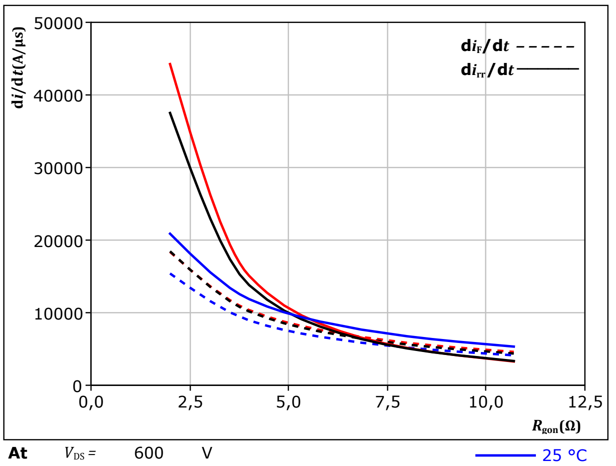


At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
R_{gon} =	5,8	Ω		150 °C

figure 39. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})

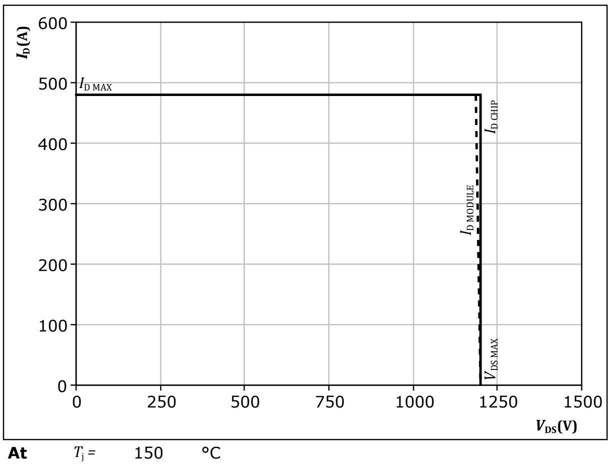


At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
I_D =	240	A		150 °C

figure 40. **MOSFET**

Reverse bias safe operating area

I_D = f(V_{DS})



At		
T_j =	150	°C
R_{gon} =	5,8	Ω
R_{goff} =	5,8	Ω

Switching Definitions

figure 41. **MOSFET**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})

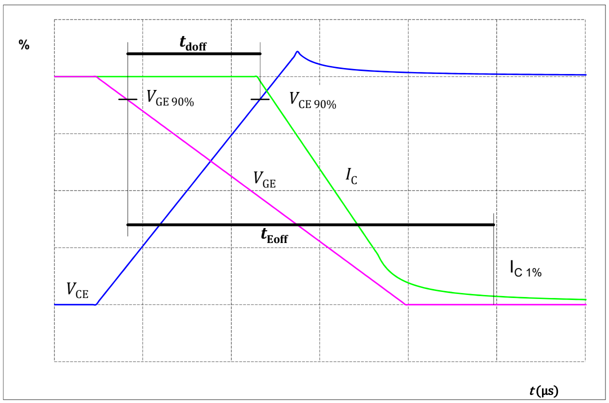


figure 42. **MOSFET**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

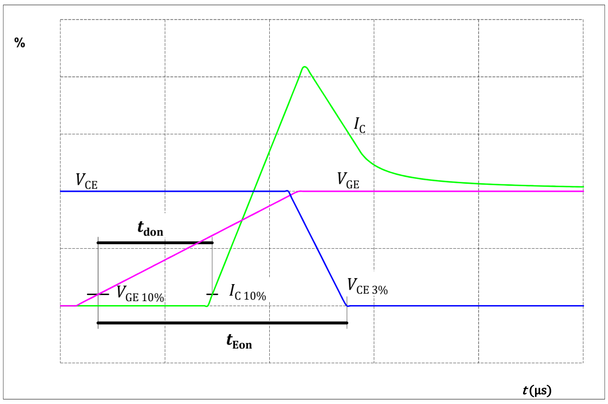


figure 43. **MOSFET**

Turn-off Switching Waveforms & definition of t_f

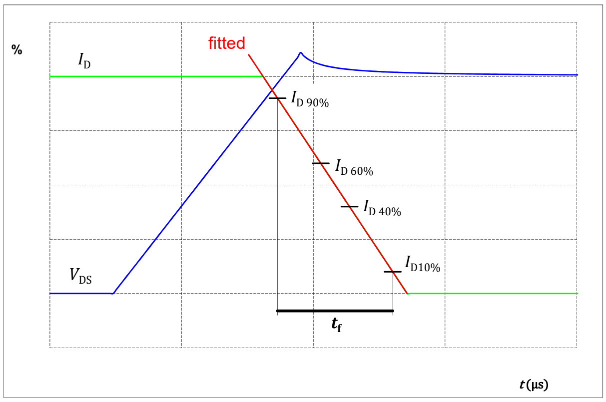
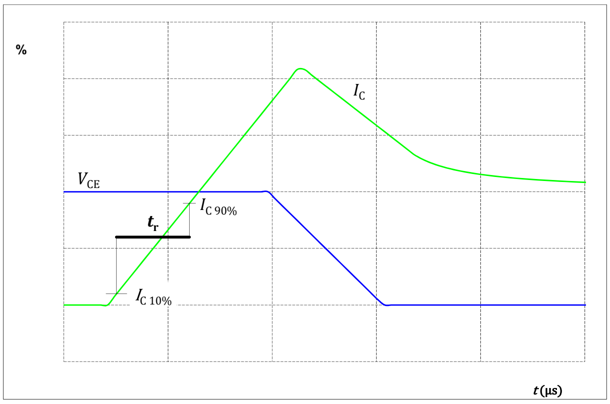


figure 44. **MOSFET**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 45. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

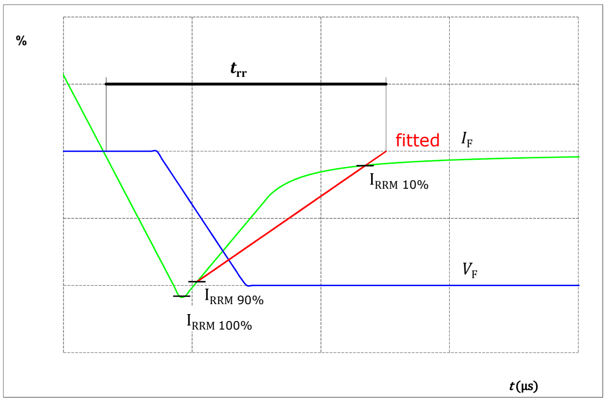


figure 46. **FWD**

Turn-on Switching Waveforms & definition of t_{Qrr} (t_{Qrr} = integrating time for Q_{rr})

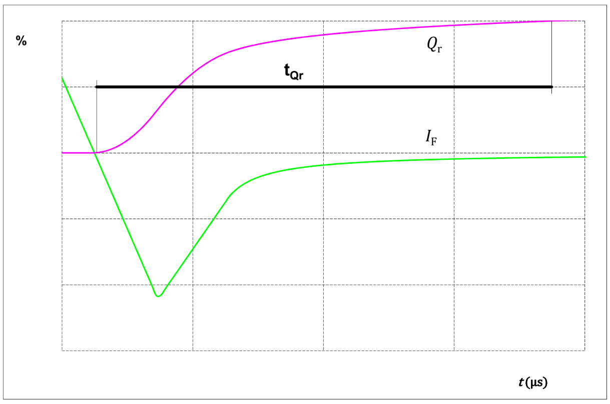
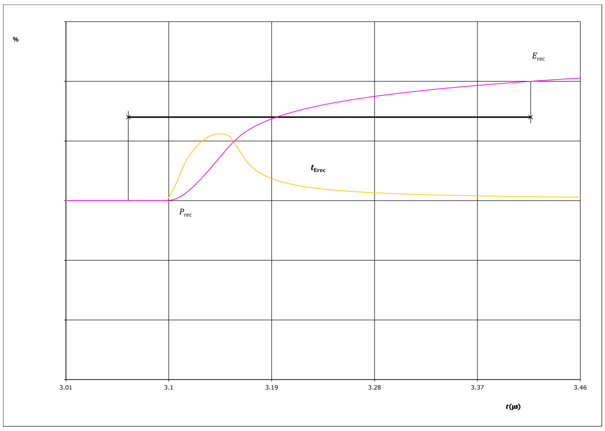


figure 47. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



10-EY122PA005ME-LU39F08T
datasheet

Vincotech

Ordering Code

Version	Ordering Code
Without thermal paste	10-EY122PA005ME-LU39F08T
With thermal paste	10-EY122PA005ME-LU39F08T-/3/

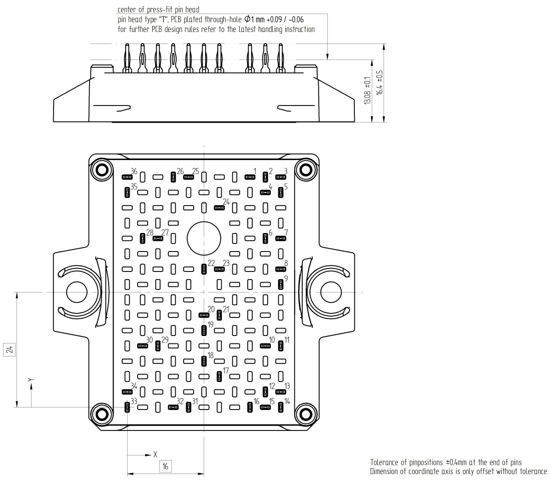
Marking

	Text	**Name**		**Date code**	**UL & VIN**	**Lot**	**Serial**
		NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
		TTTTTTTVV	LLLLL	SSSS	WWYY		

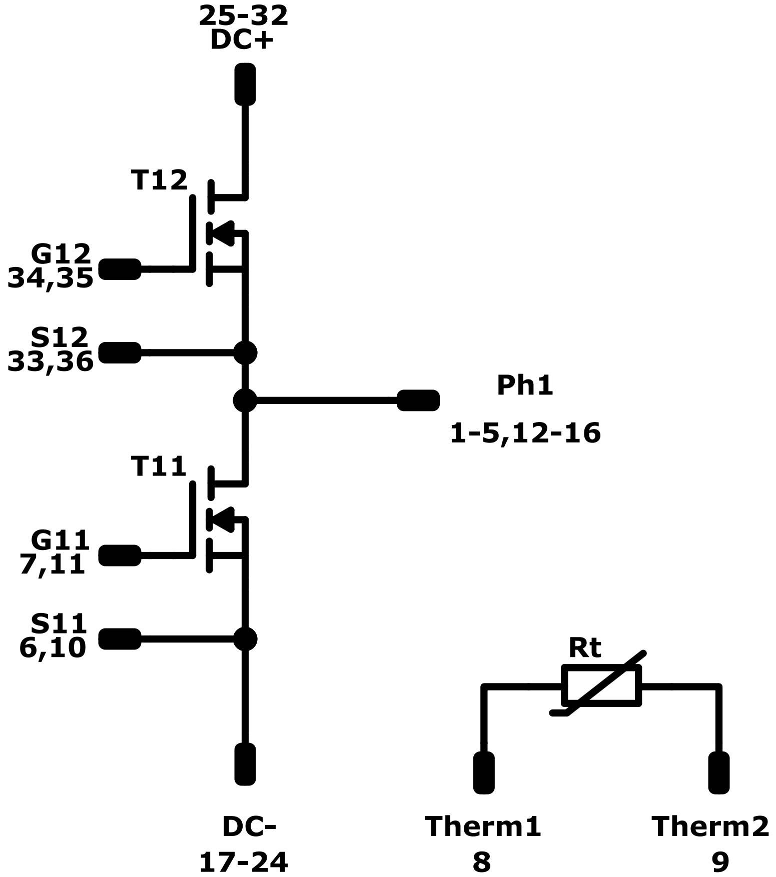
Outline

Pin	X	Y	Function
1	25,6	48	Ph1
2	28,8	48	Ph1
3	32	48	Ph1
4	28,8	44,8	Ph1
5	32	44,8	Ph1
6	28,8	35,2	S11
7	32	35,2	G11
8	32	28,8	Therm1
9	32	25,6	Therm2
10	28,8	12,8	S11
11	32	12,8	G11
12	28,8	3,2	Ph1
13	32	3,2	Ph1
14	32	0	Ph1
15	28,8	0	Ph1
16	25,6	0	Ph1
17	19,2	6,4	DC-
18	16	9,6	DC-
19	16	16	DC-
20	16	19,2	DC-
21	19,2	19,2	DC-
22	16	28,8	DC-
23	19,2	28,8	DC-
24	19,2	41,6	DC-
25	12,8	48	DC+
26	9,6	48	DC+
27	6,4	35,2	DC+
28	3,2	35,2	DC+
29	6,4	12,8	DC+
30	3,2	12,8	DC+
31	12,8	0	DC+
32	9,6	0	DC+
33	0	0	S12
34	0	3,2	G12
35	0	44,8	G12
36	0	48	S12

Pin table [mm]



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11	MOSFET	1200 V	5,33 mΩ	Half-Bridge Switch - Lo side	
T12	MOSFET	1200 V	5,33 mΩ	Half-Bridge Switch - Hi side	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* E2 packages see vincotech.com website.

Package data
Package data for *flow* E2 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-EY122PA005ME-LU39F08T-D1-14	2 Oct. 2020		

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.